

PMPB20EN

30 V N-channel Trench MOSFET

14 January 2014

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Very fast switching
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- Tin-plated 100 % solderable side pads for optical solder inspection

3. Applications

- Charging switch for portable devices
- DC-to-DC converters
- Power management in battery-driven portables
- Hard disk and computing power management

4. Quick reference data

Table 1. Quick reference data

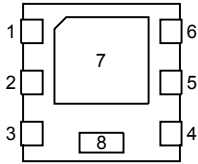
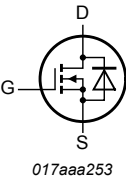
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j = 25\text{ }^{\circ}\text{C}$		-	-	30	V
V_{GS}	gate-source voltage			-20	-	20	V
I_D	drain current	$V_{GS} = 10\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}; t \leq 5\text{ s}$	[1]	-	-	10.4	A
Static characteristics							
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 7\text{ A}; T_j = 25\text{ }^{\circ}\text{C}$		-	16.5	19.5	m Ω

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	 Transparent top view DFN2020MD-6 (SOT1220)	 017aaa253
2	D	drain		
3	G	gate		
4	S	source		
5	D	drain		
6	D	drain		
7	D	drain		
8	S	source		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMPB20EN	DFN2020MD-6	DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220

7. Marking

Table 4. Marking codes

Type number	Marking code
PMPB20EN	1B

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	10.4	A
		V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	7.2	A
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	4.6	A
I _{DM}	peak drain current	T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs		-	30	A
P _{tot}	total power dissipation	T _{amb} = 25 °C	[1]	-	1.7	W
		T _{amb} = 25 °C; t ≤ 5 s	[1]	-	3.5	W
		T _{sp} = 25 °C		-	12.5	W
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain diode						
I _S	source current	T _{amb} = 25 °C	[1]	-	2.2	A

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

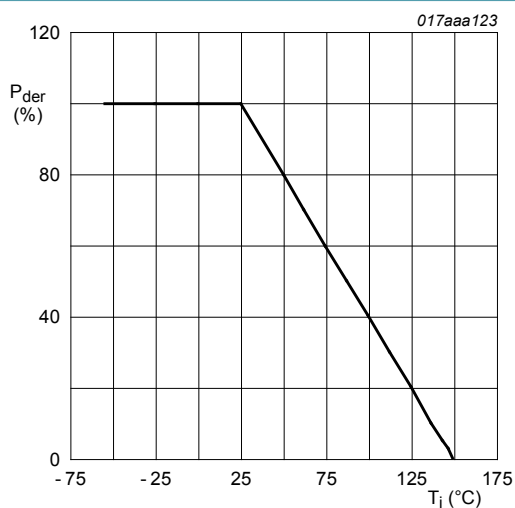


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100 \%$$

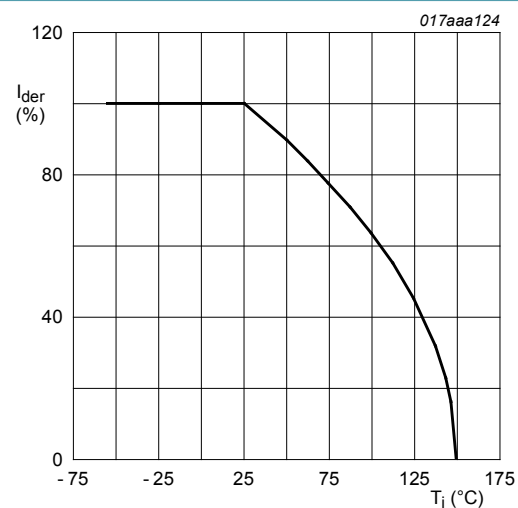
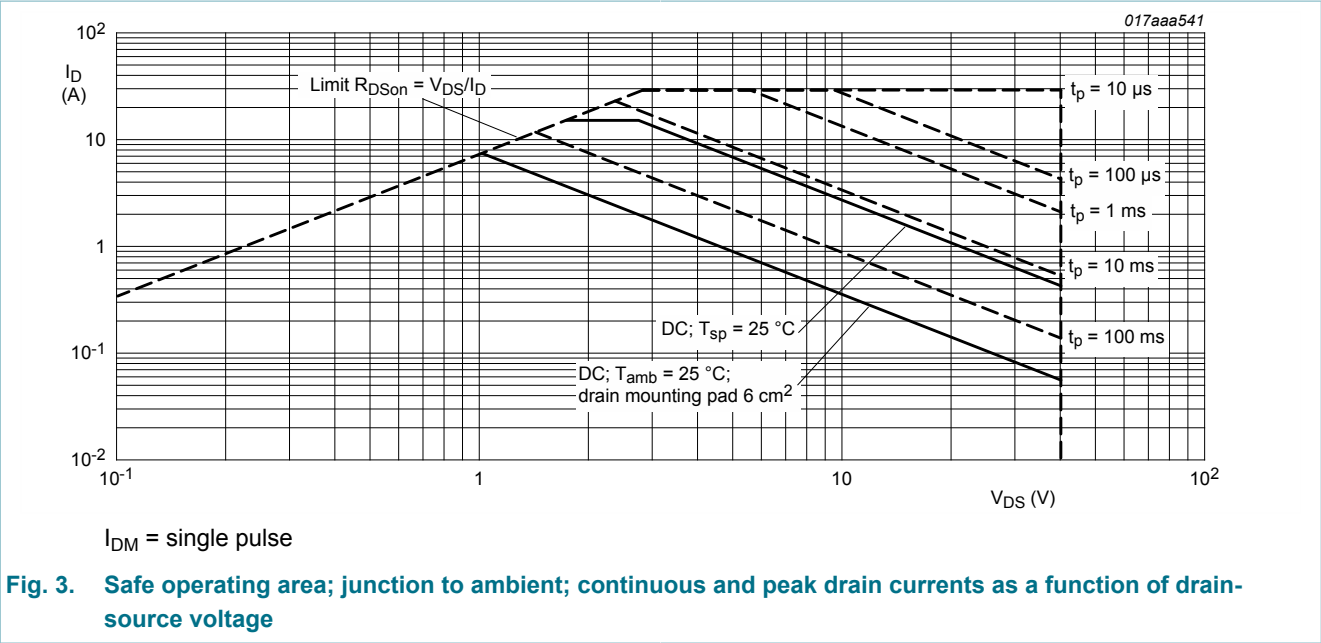


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

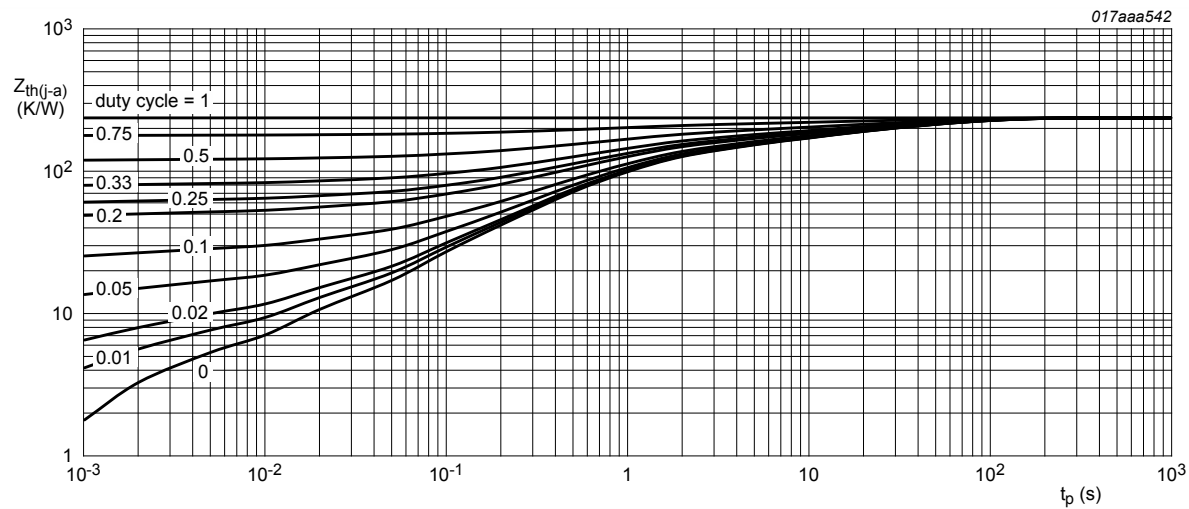


9. Thermal characteristics

Table 6. Thermal characteristics

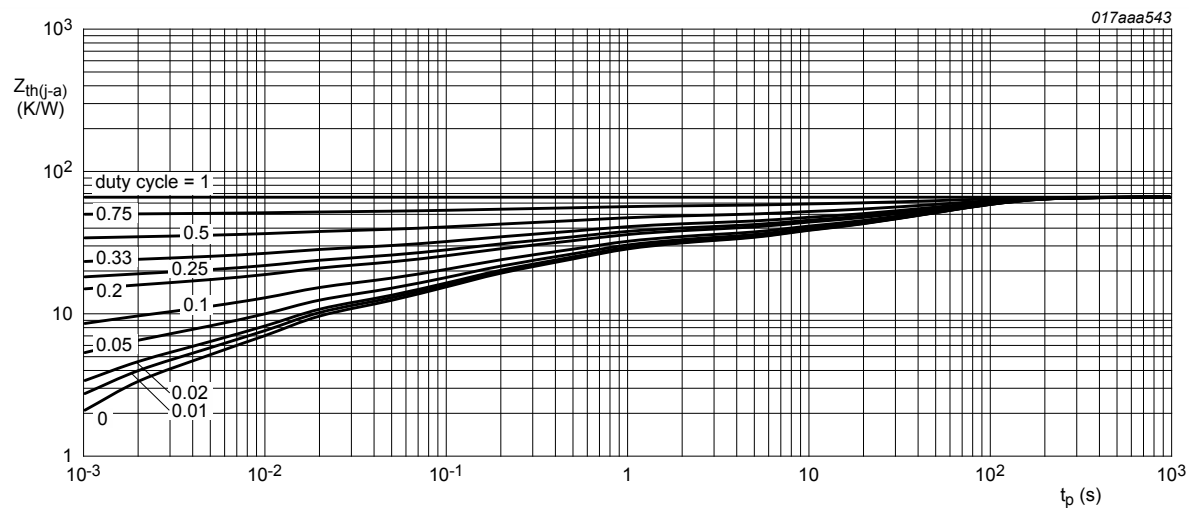
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	235	270	K/W
			[2]	-	67	74	K/W
			[3]	-	33	36	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	5	10	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm^2 .
[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm^2 , $t \leq 5\text{ s}$



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm²

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C		30	-	-	V
V _{GSth}	gate-source threshold voltage	I _D = 250 μA; V _{DS} = V _{GS} ; T _j = 25 °C		1	1.5	2	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C		-	-	1	μA
		V _{DS} = 30 V; V _{GS} = 0 V; T _j = 150 °C		-	-	20	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C		-	-	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C		-	-	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 7 A; T _j = 25 °C		-	16.5	19.5	mΩ
		V _{GS} = 10 V; I _D = 7 A; T _j = 150 °C		-	27	32	mΩ
		V _{GS} = 4.5 V; I _D = 7 A; T _j = 25 °C		-	20.5	24.5	mΩ
g _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 7 A; T _j = 25 °C		-	8	-	S
R _G	gate resistance	f = 1 MHz		-	1.7	-	Ω
Dynamic characteristics							
Q _{G(tot)}	total gate charge	V _{DS} = 15 V; I _D = 5 A; V _{GS} = 10 V; T _j = 25 °C		-	7.2	10.8	nC
Q _{GS}	gate-source charge			-	1	-	nC
Q _{GD}	gate-drain charge			-	0.67	-	nC
C _{iss}	input capacitance	V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V; T _j = 25 °C		-	435	-	pF
C _{oss}	output capacitance			-	90	-	pF
C _{rss}	reverse transfer capacitance			-	35	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 15 V; I _D = 5 A; V _{GS} = 4.5 V; R _{G(ext)} = 1.7 Ω; T _j = 25 °C		-	9	-	ns
t _r	rise time			-	17	-	ns
t _{d(off)}	turn-off delay time			-	9	-	ns
t _f	fall time			-	8	-	ns
Source-drain diode							
V _{SD}	source-drain voltage	I _S = 2.2 A; V _{GS} = 0 V; T _j = 25 °C		-	0.8	1.2	V

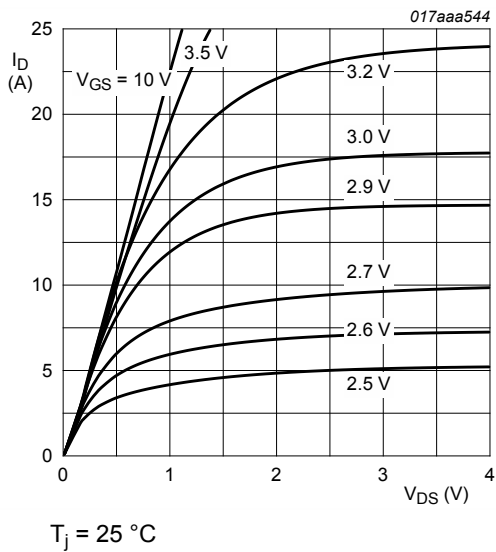


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

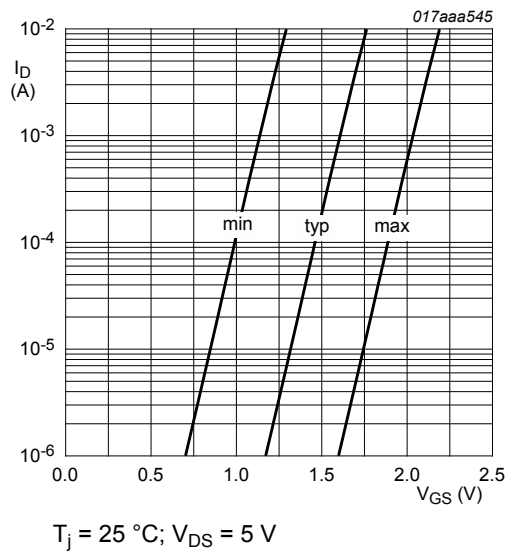


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

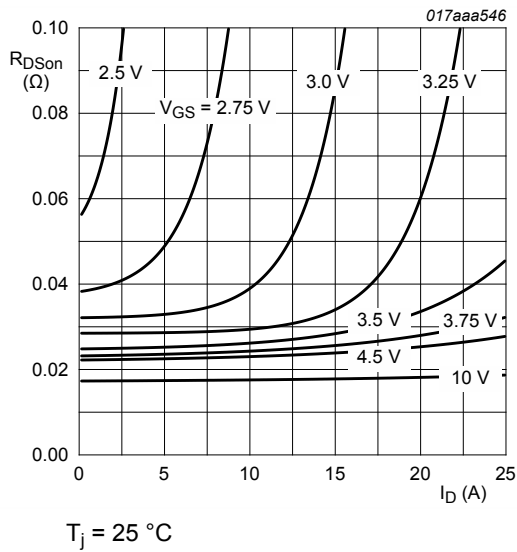


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

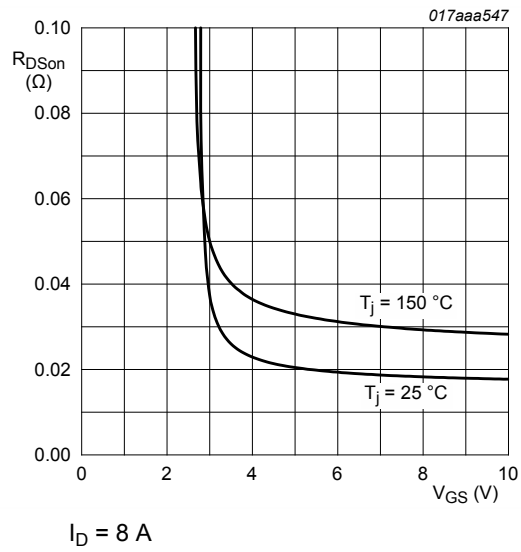


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

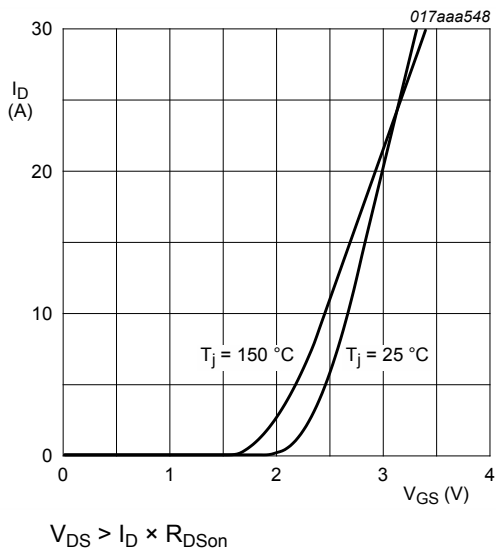


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

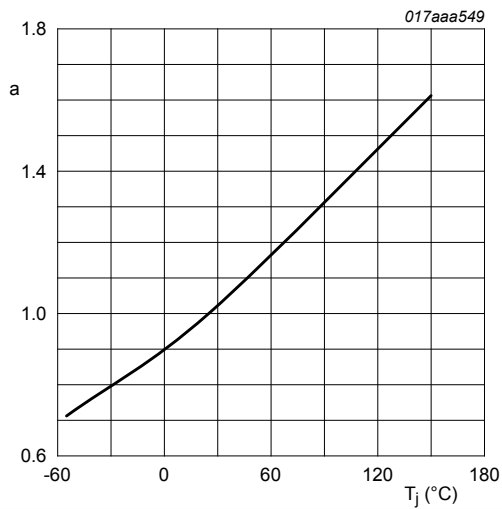


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}\text{C})}}$$

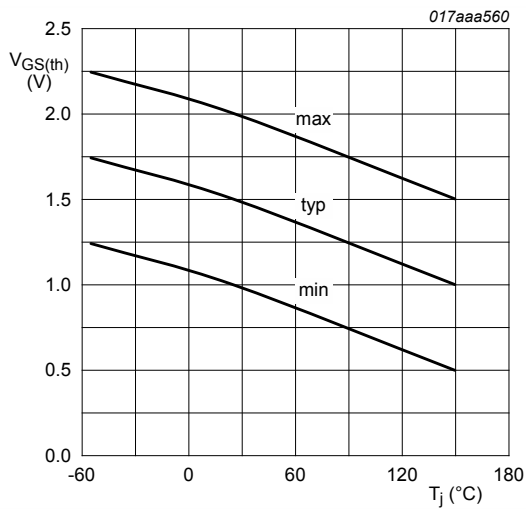


Fig. 12. Gate-source threshold voltage as a function of junction temperature

$I_D = 0.25\text{ mA}$; $V_{DS} = V_{GS}$

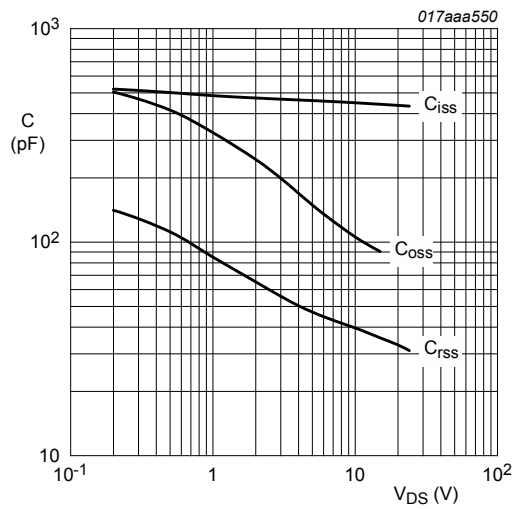


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$f = 1\text{ MHz}$; $V_{GS} = 0\text{ V}$

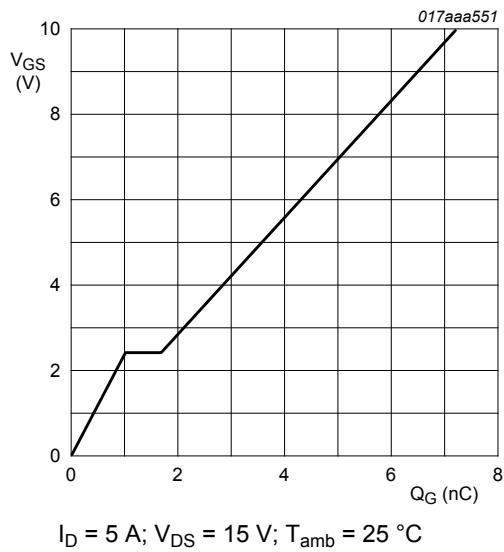


Fig. 14. Gate-source voltage as a function of gate charge; typical values

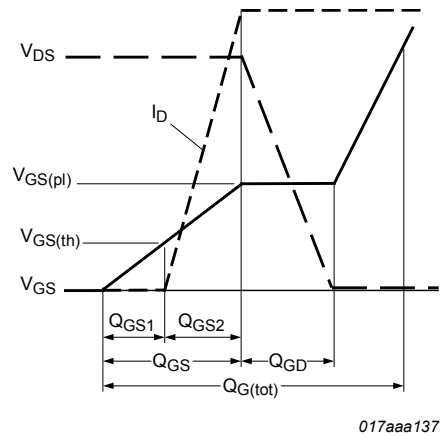


Fig. 15. Gate charge waveform definitions

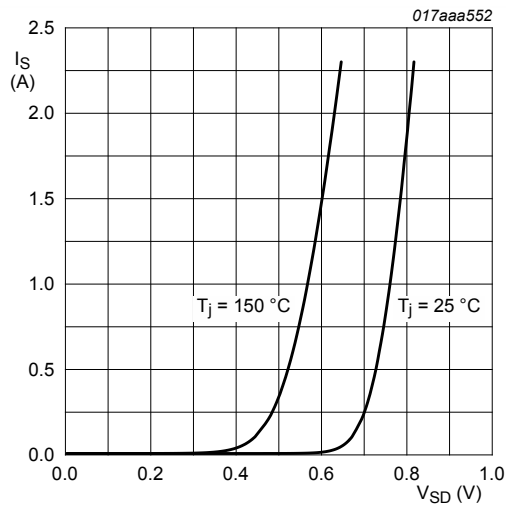


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

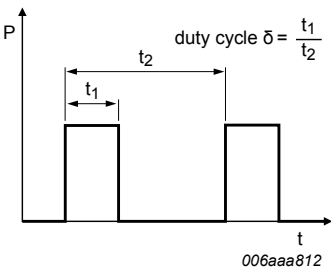


Fig. 17. Duty cycle definition

12. Package outline

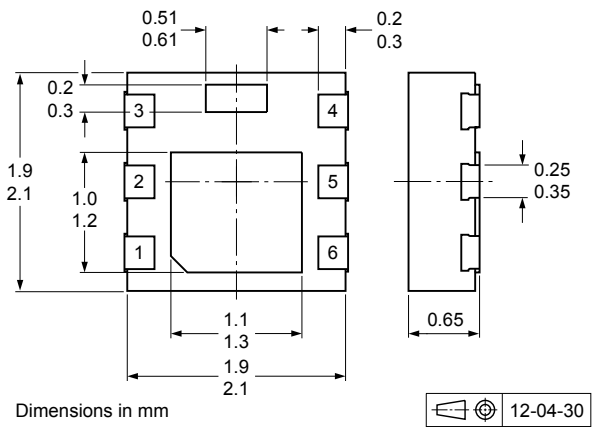
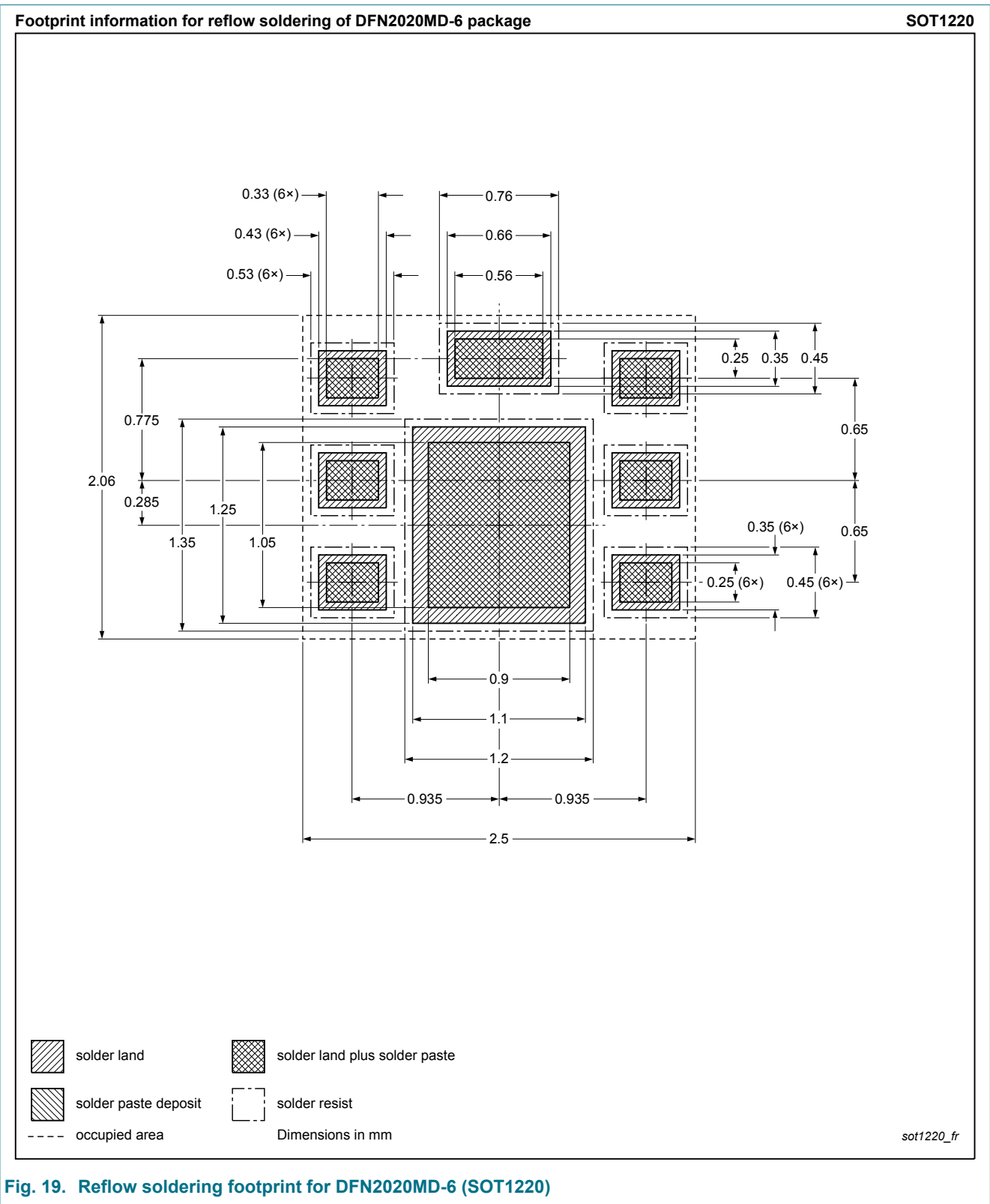


Fig. 18. Package outline DFN2020MD-6 (SOT1220)

13. Soldering



14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB20EN v.2	20140114	Product data sheet	-	PMPB20EN v.1
Modifications:	- Table 7: parameter value of V_{DS} corrected from 10 V to 15 V in capacitance condition. - Figure 16: V_{SD} parameter corrected.			
PMPB20EN v.1	20120516	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	3
9	Thermal characteristics	4
10	Characteristics	6
11	Test information	10
12	Package outline	10
13	Soldering	11
14	Revision history	12
15	Legal information	13
15.1	Data sheet status	13
15.2	Definitions	13
15.3	Disclaimers	13
15.4	Trademarks	14

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